

**IN THE SPECIFICATION:**

Please replace paragraph [0033] with the following amended paragraph:

[0033] Figure 1 shows a vertical, cross-section view of a parallel plate chemical vapor deposition processing chamber 10 having a high vacuum region 15. The processing chamber 10 contains a gas distribution manifold 11 having perforated holes for dispersing process gases there-through to a substrate (not shown). The substrate rests on a substrate support plate or susceptor 12. The susceptor 12 is mounted on a support stem 13 which connects the susceptor 12 to a lift motor 14. The lift motor 14 raises and lowers the susceptor 12 between a processing position and a lower, substrate-loading position so that the susceptor 12 (and the substrate supported on the upper surface of susceptor 12) can be controllably moved between a lower loading/off-loading position and an upper processing position which is closely adjacent to the manifold 11. When the susceptor 12 and the substrate are in the upper processing position [[14]], they are surrounded by an insulator 17.

Please replace paragraph [0076] with the following amended paragraph:

[0076] The substrate was positioned about 300 mils from the gas distribution showerhead. A power level of 600 W at a frequency of 13.56 MHz was applied [[o]] to the showerhead for plasma enhanced deposition of the films. The film was deposited at a rate of about 2,000 Å /min, and had a dielectric constant (k) of about 4.3 measured using a SSM 5100 Hg CV measurement tool at 0.1 MHz. The film also exhibited a hardness of about 0.1 GPa.

Please replace paragraph [0078] with the following amended paragraph:

[0078] The deposited film was subjected to a high temperature electron beam (e-beam) treatment using a dose of about 200  $\mu\text{C}/\text{cm}^2$   $\mu\text{C}/\text{cm}^2$ , at about 4.5 KeV and 1.5 mA, and at about 400°C. The e-beam treatment lasted for about 30 seconds.

Following the e-beam treatment, the film exhibited a dielectric constant of about 2.2 which is about 50 % less than the non-cured film. The e-beam film also exhibited a hardness of about 0.7 GPa, which is about a 600% increase compared to the non-cured film.

Please replace paragraph [0081] with the following amended paragraph:

[0081] The substrate was positioned about 300 mils from the gas distribution showerhead. A power level of 500 W at a frequency of 13.56 MHz was applied [[o]] to the showerhead for plasma enhanced deposition of the films. The film was deposited at a rate of about 1,600 Å /min, and had a dielectric constant (k) of about 4.5 measured using a SSM 5100 Hg CV measurement tool at 0.1 MHz. The film also exhibited a hardness of about 0.1 GPa.

Please replace paragraph [0083] with the following amended paragraph:

[0083] The deposited film was subjected to a high temperature electron beam (e-beam) treatment using a dose of about 200  $\mu\text{C}/\text{cm}^2$   $\mu\text{C}/\text{cm}^2$ , at about 4.5 KeV and 1.5 mA, and at about 400°C. The e-beam treatment lasted for about 30 seconds. Following the e-beam treatment, the film exhibited a dielectric constant of about 2.3 which is about 50 % less than the non-cured film. The e-beam film also exhibited a hardness of about 0.7 GPa, which is about a 600% increase compared to the non-cured film.